



Docket No.: 57454-329

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al.

Serial No.: 10/053,543✓

Filed: January 24, 2002✓

For: SEMICONDUCTOR DEVICE ?

Group Art Unit: 2814

Examiner: G. Peralta

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office
Action dated November 20, 2002.

IN THE CLAIMS:

Please amend claim 13 as follows.

12
13. (Amended) [The method according to claim 12, said source/drain of said
second transistor having a highly doped region, wherein:

the step of forming said source/drain of said second transistor includes the step of
forming first metal silicide at a surface of said heavily doped region; and

the step of forming said bit line includes the steps of: forming a plug electrode in
said first contact hole; forming second metal silicide at a surface of said plug electrode;

#6B
Amdt
SDavis
PATENT 2/25/03

RECEIVED
FEB 21 2003
TECHNOLOGY CENTER 2800

Rule
1.126 AS
B1 in Amdt A